

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-60 (Cancelled)**61. (New) A method comprising:**

adjusting a first height adjustable spacer having a first top surface so that the first top surface extends over a top surface of a hot plate by a first distance;

adjusting a second height adjustable spacer having a second top surface so that the second top surface extends over the top surface of the hot plate by a second distance, wherein the second distance is different than the first distance;

placing a substrate having an exposed radiation sensitive layer over the first and second top surfaces of the first and second height adjustable spacers; and

heating the radiation sensitive layer with the hot plate.

62. (New) The method of claim 61, wherein said adjusting the first height adjustable spacer comprises turning a screw.

63. (New) The method of claim 61, wherein said adjusting the first height adjustable spacer comprises adjusting a voltage input to a piezoelectric substance.

64. (New) The method of claim 61, further comprising determining the first distance based on sizing errors of critical dimensions in a region of the exposed radiation sensitive layer proximate the first height adjustable spacer.

65. (New) The method of claim 61, wherein said heating comprises reducing errors in the exposed radiation sensitive layer.
66. (New) The method of claim 65, wherein said heating comprises heating a critical dimension undersizing error to a greater temperature than a critical dimension oversizing error in a negative acting, chemically amplified resist.
67. (New) The method of claim 61, further comprising coupling a surface of the substrate with an insulator that is coupled with the first height adjustable spacer.
68. (New) The method of claim 61, further comprising placing a solid having the first height adjustable spacer coupled thereto in a void in the hot plate.
69. (New) The method of claim 61, wherein the radiation sensitive layer comprises a negative acting, chemically amplified resist.
70. (New) A method comprising:

placing a substrate having a resist layer over a top surface of a hot plate so that different regions of the resist layer are separated from the top surface of the hot plate by different distances; and

heating the resist layer by transferring different quantities of heat from the top surface of the hot plate to the different regions of the resist layer.
71. (New) The method of claim 70, further comprising:

turning a screw; and

supporting the substrate on the turned screw.

72. (New) The method of claim 70, further comprising:
 - adjusting a voltage input to a piezoelectric substance; and
 - supporting the substrate on the piezoelectric substance having the adjusted voltage input.
73. (New) The method of claim 70, further comprising determining the different distances based on sizing errors of critical dimensions in the regions.
74. (New) The method of claim 70, wherein said heating comprises reducing exposure errors in the resist layer.
75. (New) The method of claim 70, wherein said heating comprises heating a critical dimension undersizing error to a greater temperature than a critical dimension oversizing error in a negative acting, chemically amplified resist layer.
76. (New) The method of claim 70, wherein said placing comprises placing the substrate into contact with an insulator that is coupled with a height adjustable spacer.
77. (New) The method of claim 70, wherein the resist layer comprises a negative acting, chemically amplified resist.